

ABSTRACT

A semiconductor device includes an insulation film **6** formed on a silicon substrate **1**, a buried interconnect **10** formed in the insulation film **6**, and a barrier metal film **A1** formed between the insulation film **6** and the buried interconnect **10**. The barrier metal film **A1** is formed of a lamination layer of a metal compound film **7** and a metal film **9** which does not lose its conductivity when being oxidized. In the vicinity of an interface between the metal compound film **7** and the metal film **9**, a fusion layer **8** obtained through fusion of the metal compound film **7** and the metal film **9** is provided.